

ABSTRACT

A light emitting apparatus 10 includes an aluminum nitride co-fired substrate 11 and a light emitting device 12 arranged on a front surface of the co-fired substrate, in  
5 which the front surface of the aluminum nitride substrate 11 bearing the light emitting device 12 is mirror-polished so as to have a surface roughness of  $0.3\ \mu\text{m Ra}$  or less, and the light emitting apparatus 10 further includes a vapor-deposited metal film 14 and via holes 15. The vapor-deposited metal film 14 is arranged on the front surface of the aluminum nitride substrate 11 around the light emitting device 12 and has a  
10 reflectivity of 90% or more with respect to light emitted from the light emitting device 12. The via holes 15 penetrates the aluminum nitride substrate 11 from the front surface bearing the light emitting device 12 to the rear surface to thereby allow conduction to the light emitting device 12 from the rear surface. This configuration can reduce light emitting apparatuses in size and can provide light emitting  
15 apparatuses that are excellent in heat radiation performance, allow a larger current to pass therethrough, and can have a significantly increased luminance with a high luminous efficiency.